

Silicon NPN Power Transistors

2SC3762

DESCRIPTION

- With TO-3PML package
- High speed switching
- High current capability

APPLICATIONS

- For use in high speed and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

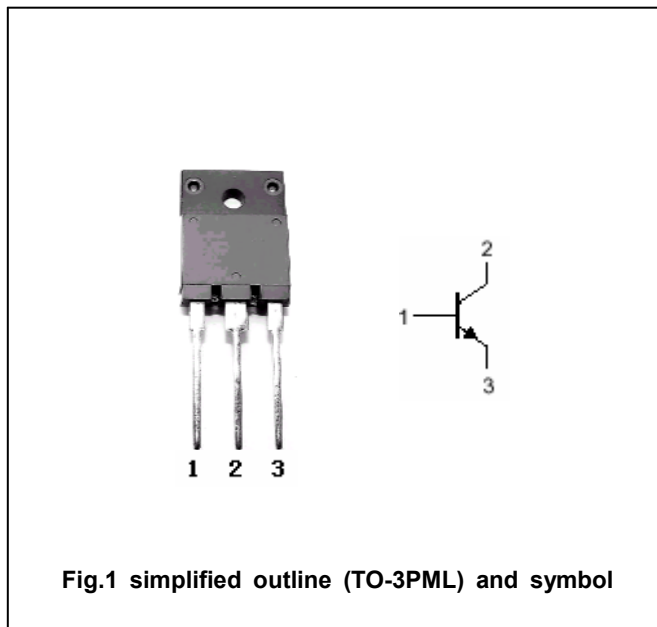


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		15	A
P _C	Collector dissipation	T _C =25°C	65	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA ; I_B=0$	100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=10A ; I_B=1A$			0.6	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=10A ; I_B=1A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=100V ; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=4V ; I_C=0$			10	μA
h_{FE}	DC current gain	$I_C=5A ; V_{CE}=5V$	30		120	

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PACKAGE OUTLINE

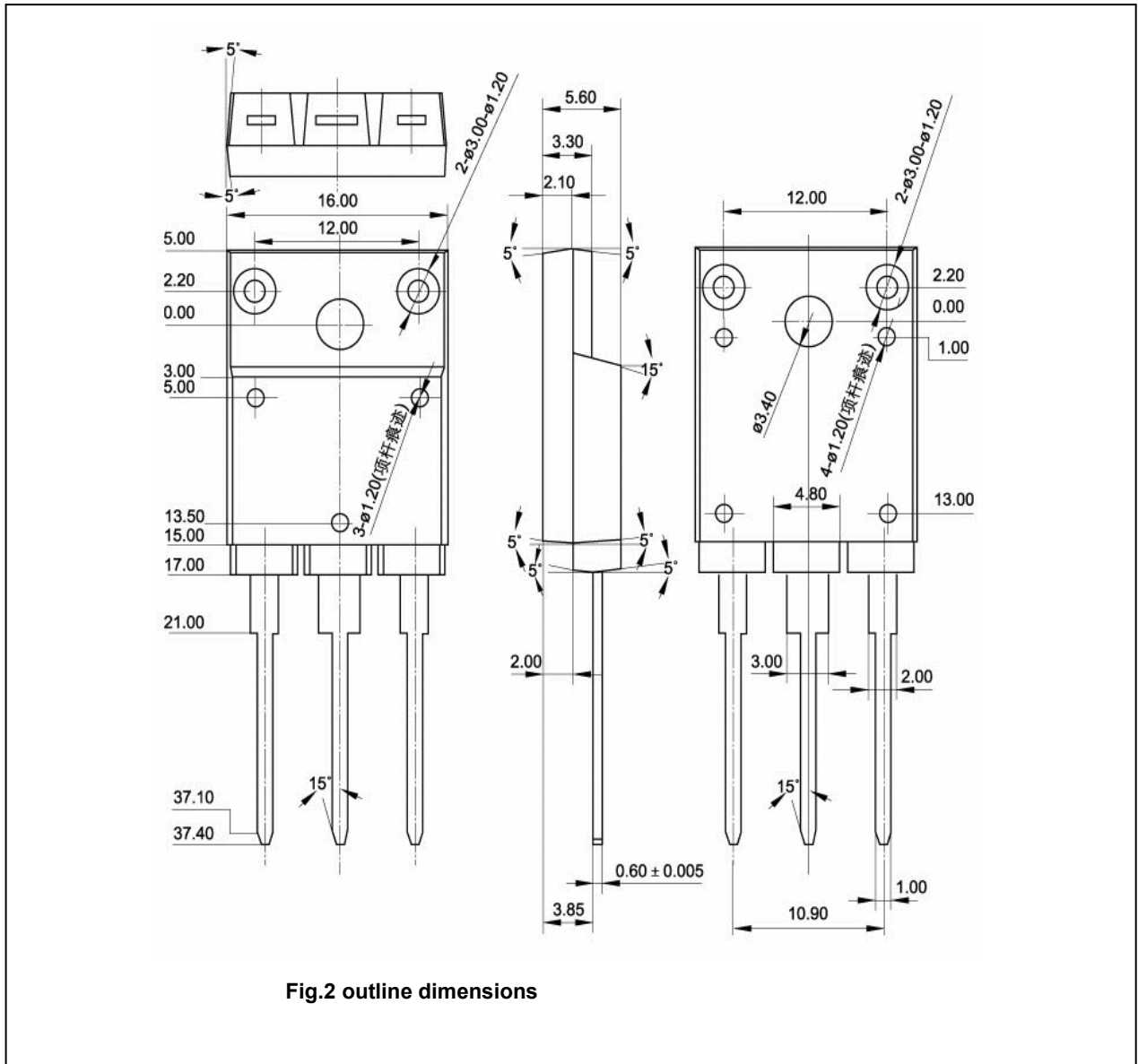


Fig.2 outline dimensions